

**AMENDMENTS TO THE CLAIMS**

This listing of claims replaces all prior listing of claims in this application.

Claims 1-12 (Canceled).

13. (Currently amended) A semiconductor device comprising:

a substrate;

an oxide layer formed over said substrate;

a layer that is transparent to light formed over said substrate and having a first thickness, wherein said transparent layer includes a material selected from the group consisting of BPSG, PSG, and TEOS; and

a first anti-reflective coating formed beneath the transparent layer and on said oxide layer and having a second thickness, wherein said first thickness is greater than the second thickness.

14. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating has a complex refractive index with an imaginary part whose value is at least one.

Claims 15-16 (Canceled).

17. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating includes a material comprising an organic polymer.

18. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating includes a material comprising silicon and nitrogen.

19. (Original) The semiconductor device of claim 13 wherein the first anti-reflective coating includes a material comprising silicon and oxygen.

20. (Original) The semiconductor device of claim 13 further including:

a second anti-reflective coating extending over the transparent layer.

21. (Currently amended) A semiconductor device comprising:

a substrate;

an oxide layer formed over said substrate;

a layer that is transparent to light formed over said substrate and having a wavelength of approximately 365 nm, wherein said transparent layer includes a material selected from the group consisting of BPSG, PSG and TEOS; and

a first anti-reflective coating formed beneath the transparent layer and on said oxide layer.

22. (Original) The semiconductor device of claim 21 wherein the first anti-reflective coating has a complex refractive index with an imaginary part whose value is at least one.

23-24 (Canceled).

25. (Original) The semiconductor device of claim 21 wherein the first anti-reflective coating includes a material comprising silicon and nitrogen.

26. (Original) The semiconductor device of claim 21 wherein the first anti-reflective coating includes a material comprising silicon and oxygen.

27. (Original) The semiconductor device of claim 21 further including:

a second anti-reflective coating extending over the transparent layer.

28. (Currently amended) A semiconductor device comprising:

a substrate;

an oxide layer formed over said substrate;

a layer that is transparent to light formed over said substrate and having a wavelength of approximately 193 nm, wherein said transparent layer includes a material selected from the group consisting of BPSG, PSG and TEOS; and

a first anti-reflective coating beneath the transparent layer and on said oxide layer.

29. (Original) The semiconductor device of claim 28 wherein the first anti-reflective coating has a complex refractive index with an imaginary part whose value is at least one.

Claims 30-31 (Canceled).

32. (Original) The semiconductor device of claim 28 wherein the first anti-reflective coating includes a material comprising silicon and nitrogen.

33. (Original) The semiconductor device of claim 28 wherein the first anti-reflective coating includes a material comprising silicon and oxygen.

34. (Original) The semiconductor device of claim 28 further including:

a second anti-reflective coating extending over the transparent layer.

35. (Previously presented) The semiconductor device of claim 20 wherein the second anti-reflective coating includes a material comprising silicon and nitrogen.

36. (Previously presented) The semiconductor device of claim 20 wherein the second anti-reflective coating includes a material comprising silicon and oxygen.

37. (Previously presented) The semiconductor device of claim 20 wherein the second anti-reflective coating includes a material comprising an organic polymer.

38. (Previously presented) The semiconductor device of claim 27 wherein the second anti-reflective coating includes a material comprising silicon and nitrogen.

39. (Previously presented) The semiconductor device of claim 27 wherein the second anti-reflective coating includes a material comprising silicon and oxygen.

40. (Previously presented) The semiconductor device of claim 27 wherein the second anti-reflective coating includes a material comprising an organic polymer.

41. (Previously presented) The semiconductor device of claim 34 wherein the second anti-reflective coating includes a material comprising silicon and nitrogen.

42. (Previously presented) The semiconductor device of claim 34 wherein the second anti-reflective coating includes a material comprising silicon and oxygen.

43. (Previously presented) The semiconductor device of claim 34 wherein the second anti-reflective coating includes a material comprising an organic polymer.

44. (Currently amended) A semiconductor device comprising:

a silicon oxide layer formed over a surface of a substrate;

an anti-reflective coating layer ~~having a first thickness~~ formed ~~[[over]]~~ on said silicon oxide layer; and

a layer which is transparent to the wavelength of light formed over the anti-reflective coating layer, ~~said transparent layer having a second thickness greater than said first thickness, and wherein said transparent layer includes a material selected from the group consisting of BPSG, PSG and TEOS.~~

45. (Previously Presented) The semiconductor device of claim 13, wherein said transparent layer is transparent to light having a wavelength of approximately 248 nm.

Claims 46-55 (Canceled).

56. (New) A semiconductor device comprising:

a layer formed over a substrate that is transparent to light having a first thickness, wherein said transparent layer includes an oxide material selected from the group consisting of BPSG, PSG, and TEOS; and

a first anti-reflective coating formed beneath the transparent layer having a second thickness, wherein said first thickness is greater than the second thickness.

57. (New) A semiconductor device comprising:

a layer formed over a substrate that is transparent to light having a wavelength of approximately 365 nm, wherein said transparent layer includes an oxide material selected from the group consisting of BPSG, PSG and TEOS; and

a first anti-reflective coating formed beneath the transparent layer.

58. (New) A semiconductor device comprising:

a layer formed over a substrate that is transparent to light having a wavelength of approximately 193 nm, wherein said transparent layer includes an oxide material selected from the group consisting of BPSG, PSG and TEOS; and

a first anti-reflective coating beneath the transparent layer.